

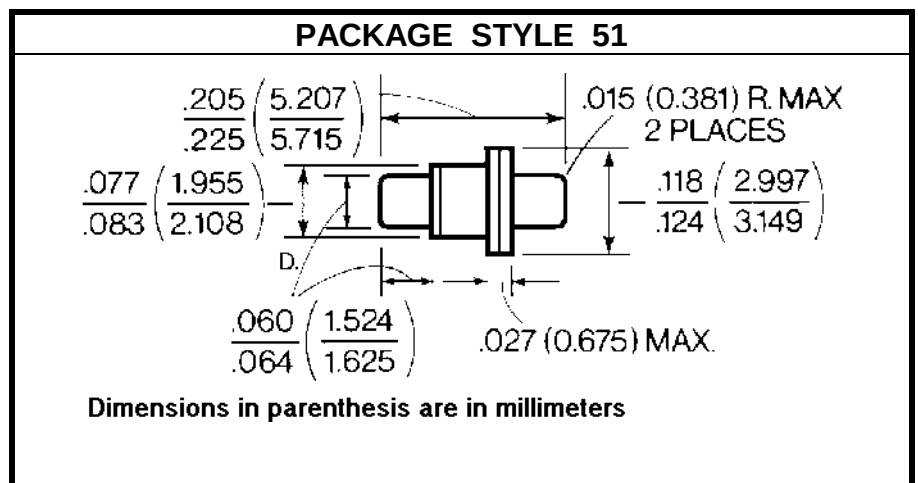
SILICON MULTIPLIER DIODE

DESCRIPTION:

The **ASI BXY56** is a Varactor Diode Designed for Operation in Low and High Order Multiplier Circuits.

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	60 V
P_{DISS}	5.2 W @ $T_C = 50^\circ\text{C}$
T_J	-55°C to $+175^\circ\text{C}$
T_{STG}	-55°C to $+175^\circ\text{C}$
θ_{JC}	24°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	$I_R = 10 \mu\text{A}$	60			V
C_j	$V_R = -6.0 \text{ V}$ $f = 1.0 \text{ MHz}$	1.5		2.5	pF
f_{c-6}	$V_R = 6.0 \text{ V}$ $f = 10 \text{ GHz}$	160			GHz
T_i	6.0 mA / 10 mA		60		μS
T_t	10 V / 10 mA			350	pS
MARKING	INK DOT INDICATES CATHODE END				